

## **DATASHEET**

# 1.9mm Round Subminiature Axial Phototransistor PT91-21B



#### **Features**

- Fast response time
- High photo sensitivity
- Small junction capacitance
- Compatible with infrared and vapor phase reflow solder process.
- Pb free
- RoHS Compliance
- The product itself will remain within RoHS compliant version.

## **Descriptions**

• PT91-21B is a phototransistor in miniature SMD package which is molded in black transparent epoxy with spherical top view lens. The device is spectrally matched to infrared emitting diode.

## **Applications**

- Miniature switch
- Counters and sorter
- Position sensor
- Infrared applied system

#### **Device Selection Guide**

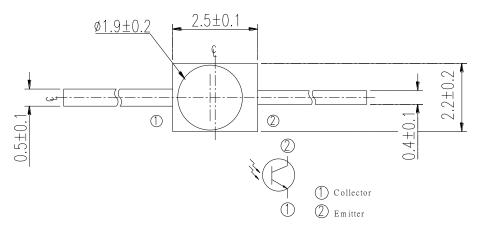
Part Category	Chip Material	Lens Color
PT	Silicon	Black

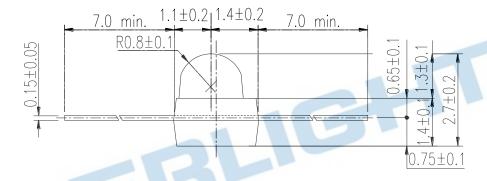
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# **Package Dimensions**





Notes: 1. All dimensions are in millimeters

2.Tolerances unless dimensions ±0.1mm

# Absolute Maximum Ratings (Ta=25 $^{\circ}$ C)



Parameter	Symbol	Symbol Rating	
Collector-Emitter Voltage	$V_{CEO}$	30	V
Emitter-Collector-Voltage	$V_{ECO}$	5	V
Collector Current	$I_{C}$	20	mA
Operating Temperature	$T_{opr}$	-25 ~ +85	$^{\circ}\!\mathbb{C}$
Storage Temperature	$T_{stg}$	-40 ~ + 85	$^{\circ}\!\mathbb{C}$
Soldering Temperature *1	$T_{sol}$	260	$^{\circ}\!\mathbb{C}$
Power Dissipation at(or below) 25°C Free Air Temperature	$P_d$	75	mW

**Notes:** \*1:Soldering time ≤ 5 seconds.

# **Electro-Optical Characteristics (Ta=25°C)**

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Rang Of Spectral Bandwidth	λ 0.5		730		1100	nm
Wavelength Of Peak Sensitivity	$\lambda_{ m P}$			940		nm
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	$I_{C}=100\mu A$ Ee=0mW/cm <sup>2</sup>	30			V
Emitter-Collector Breakdown Voltage	$\mathrm{BV}_{\mathrm{ECO}}$	$I_E=10\mu A$ $Ee=0mW/cm^2$	5			V
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =2mA Ee=1mW/cm <sup>2</sup>			0.4	V
Collector Dark Current	$I_{CEO}$	V <sub>CE</sub> =20V Ee=0mW/cm <sup>2</sup>			100	nA
On State Collector Current	$I_{C(ON)}$	V <sub>CE</sub> =5V Ee=1mW/cm <sup>2</sup>	1.0	3.0		mA



## **Typical Electro-Optical Characteristics Curves**

Fig.1 Spectral Sensitivity

Segretary Sensitivity

0.8

0.8

0.6

0.4

0.2

700 800 900 1000 1100 1300

Wavelength λ (nm)

Fig.2 Collector Current vs.
Irradiance

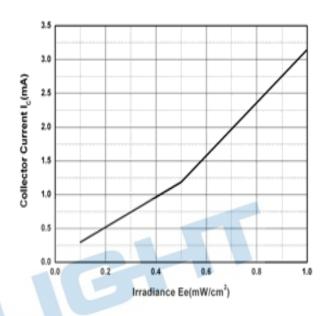
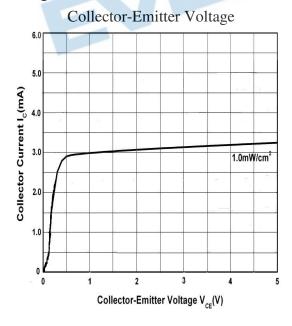


Fig.3 Collector Current vs.





### **Precautions For Use**

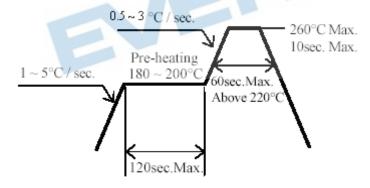
1. Over-current-proof

Customer must apply resistors for protection, otherwise slight voltage shift will cause big current change (Burn out will happen).

- 2. Storage
- 2.1 Do not open moisture proof bag before the products are ready to use.
- 2.2 Before opening the package, the Phototransistor should be kept at 30°C or less and 90%RH or less.
- 2.3 The Phototransistor should be used within a year.
- 2.4 After opening the package, the Phototransistor should be kept at 30°C or less and 60%RH or less.
- 2.5 The Phototransistor should be used within 168 hours (7 days) after opening the package.
- 2.6 If the moisture absorbent material (silica gel) has faded away or the Phototransistor have exceeded the storage time, baking treatment should be performed using the following conditions.

Baking treatment :  $60\pm5^{\circ}$ C for 24 hours.

- 3. Soldering Condition
- 3.1 Pb-free solder temperature profile



- 3.2 Reflow soldering should not be done more than two times.
- 3.3 When soldering, do not put stress on the Phototransistor during heating.
- 3.4 After soldering, do not warp the circuit board.

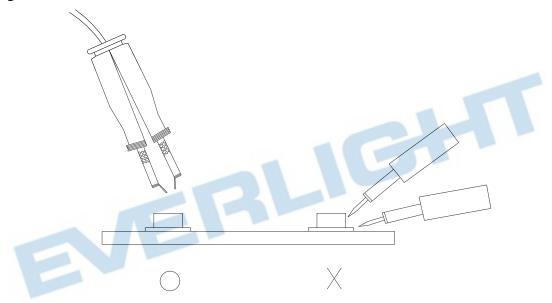


## 4. Soldering Iron

Each terminal is to go to the tip of soldering iron temperature less than  $350^{\circ}$ C for 3 seconds within once in less than the soldering iron capacity 25W. Leave two seconds and more intervals, and do soldering of each terminal. Be careful because the damage of the product is often started at the time of the hand solder.

## 5.Repairing

Repair should not be done after the Phototransistor have been soldered. When repairing is unavoidable, a double-head soldering iron should be used (as below figure). It should be confirmed beforehand whether the characteristics of the Phototransistor will or will not be damaged by repairing.



# **Packing Quantity Specification**

1000PCS/1Bag



## **Label Form Specification**



CPN: Customer's Production Number

P/N: Production Number QTY: Packing Quantity

CAT: Ranks

**HUE: Peak Wavelength** 

**REF: Reference** 

LOT No: Lot Number

#### **Notes**

- Above specification may be changed without notice. EVERLIGHT will reserve authority on material change for above specification.
- 2. When using this product, please observe the absolute maximum ratings and the instructions for using outlined in these specification sheets. EVERLIGHT assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
- 3. These specification sheets include materials protected under copyright of EVERLIGHT corporation. Please don't reproduce or cause anyone to reproduce them without EVERLIGHT's consent.

EVERLIGHT ELECTRONICS CO., LTD.

Office: No. 6-8, Zhonghua Rd., Shulin Dist.,

New Taipei City 23860, Taiwan

Tel: 886-2-2685-6688

Fax: 886-2685-2699 , 6897

http://www.everlight.com